



BCV47Q

60V NPN DARLINGTON TRANSISTOR IN SOT23

Description

This Bipolar Junction Transistor (BJT) is designed to meet the stringent requirements of automotive applications.

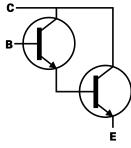
Features

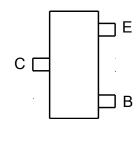
- BV_{CEO} > 60V
- Darlington Transistor h_{FE} > 10k @ 100mA for High Gain
- I_C = 500mA High Continuous Collector Current
- Complementary Darlington PNP Type: BCV46
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability
- PPAP Capable (Note 4)

Mechanical Data

- Case: SOT23
- Case Material: Molded Plastic, "Green" molding compound
- UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Plated Leads, Solderable per MIL-STD-202, Method 208 (23)
- Weight 0.008 grams (Approximate)







Top View Pin-Out

Ordering Information (Notes 4 & 5)

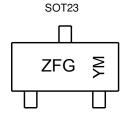
Part Number	Compliance	Marking	Reel size (inches)	Tape width (mm)	Quantity per reel
BCV47QTA	Automotive	ZFG	7	8	3,000
BCV47QTC	Automotive	ZFG	13	8	10,000

Device Symbol

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- 2. See http://www.diodes.com for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. Automotive products are AEC-Q101 qualified and are PPAP capable. Refer to http://www.diodes.com/quality/product_compliance_definitions/.
- 5. For packaging details, go to our website at http://www.diodes.com.

Marking Information



ZFG = Product Type Marking Code YM = Date Code Marking Y or \overline{Y} = Year (ex: E = 2017) M or \overline{M} = Month (ex: 9 = September)

Date Code Key

Year	2017	2018	2019	2020	2021	2022	2023	2024	2025	2026	2027	2028
Code	Е	F	G	Η	-	J	K	L	М	N	0	Р
	1								1	1	1	
Month	lon	Feb	Mar	Anr	May	1	11	Aug	Sep	Oct	Nov	Dec
WOITH	Jan	гер	Iviai	Apr	way	Jun	Jul	Aug	Sep	Ö	INOV	Dec



Absolute Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V_{CBO}	80	V
Collector-Emitter Voltage	V_{CEO}	60	V
Emitter-Base Voltage	V_{EBO}	10	V
Continuous Collector Current	Ic	500	mA
Peak Pulse Current	I _{CM}	800	mA
Base Current	I _B	100	mA

Thermal Characteristics (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit		
Power Dissipation	(Note 6)	D-	310	mW	
Fower Dissipation	(Note 7)	P _D	350	11100	
Thermal Resistance, Junction to Ambient	(Note 6)	D	403	°C/W	
Thermal Resistance, Junction to Ambient	(Note 7)	$R_{\theta JA}$	357	G/VV	
Thermal Resistance, Junction to Leads (Note 8)		$R_{ heta JL}$	350	°C/W	
Operating and Storage Temperature Range		$T_{J,}T_{STG}$	-55 to +150	°C	

ESD Ratings (Note 9)

Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	2,000	V	2
Electrostatic Discharge - Machine Model	ESD MM	200	٧	В

Notes:

- 6. For the device mounted on minimum recommended pad layout FR4 PCB with high coverage of single sided 1oz copper in still air condition; the device is measured when operating in a steady-state condition.

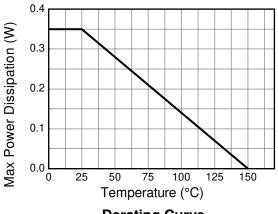
 7. Same as note (6), except the device is mounted on 15mm x 15mm FR4 PCB.

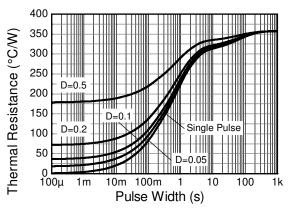
 8. Thermal resistance from junction to solder-point (at the end of the leads).

 9. Refer to JEDEC specification JESD22-A114 and JESD22-A115.



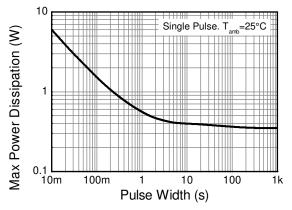
Thermal Characteristics and Derating Information (@TA = +25°C, unless otherwise specified.)





Derating Curve

Transient Thermal Impedance



Pulse Power Dissipation



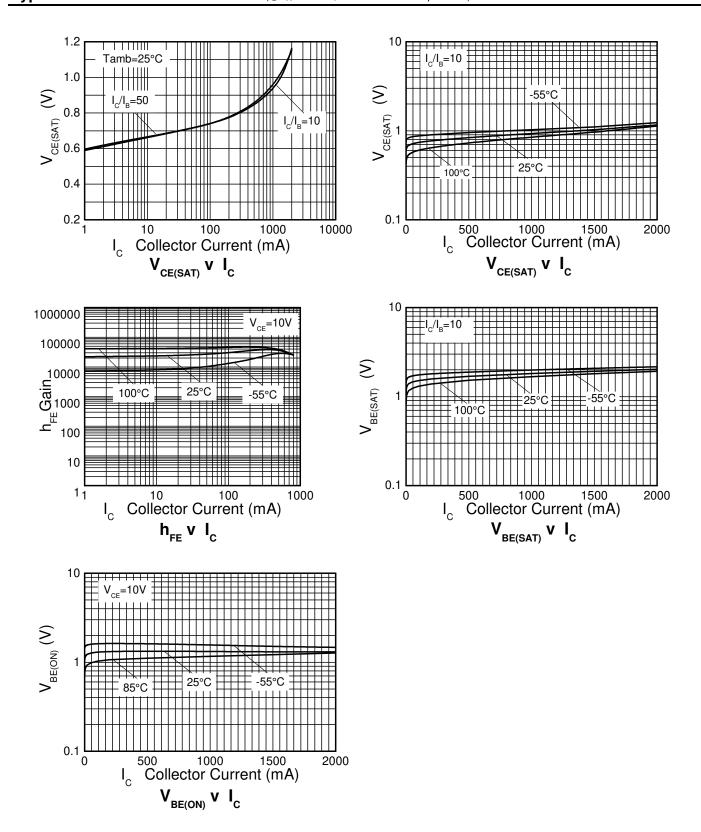
Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
OFF CHARACTERISTICS						
Collector-Base Breakdown Voltage	BV_CBO	80		_	V	$I_C = 100\mu A$
Collector-Emitter Breakdown Voltage (Note 10)	BV _{CEO}	60	_	_	V	I _{CEO} = 10mA
Emitter-Base Breakdown Voltage	BV _{EBO}	10	_	_	V	$I_{EBO} = 10\mu A$
Collector cut-off current	lone	_	<1	100	nA	V _{CB} = 60V
Collector cut-on current	I _{CBO}	_	_	10	μΑ	$V_{CB} = 60V, T_A = +150^{\circ}C$
Emitter-base Cut-off Current	I _{EBO}		<1	100	nA	$V_{EB} = 4V$
ON CHARACTERISTICS (Note 10)						
Static Forward Current Transfer Ratio	h _{FE}	2,000 4,000 10,000 2,000	_	_	_	$\begin{split} &I_{C} = 100 \mu A, \ V_{CE} = 1 V \\ &I_{C} = 10 m A, \ V_{CE} = 5 V \\ &I_{C} = 100 m A, \ V_{CE} = 5 V \\ &I_{C} = 500 m A, \ V_{CE} = 5 V \end{split}$
Collector-Emitter Saturation Voltage	V _{CE(sat)}	_	_	1.0	V	I _C = 100mA, I _B = 0.1mA
Base-Emitter Saturation Voltage	V _{BE(sat)}	_	_	1.5	V	I _C = 100mA, I _B = 0.1mA
SMALL SIGNAL CHARACTERISTICS (Note 10)						
Transition Frequency	f _T	_	170	_	MHz	$I_C = 50$ mA, $V_{CE} = 5$ V, $f = 20$ MHz
Output Capacitance	C_obo	_	3.5	_	pF	$V_{CB} = 10V$, $f = 1MHz$

Note: 10. Measured under pulsed conditions. Pulse width \leq 300 μ s. Duty cycle \leq 2%.



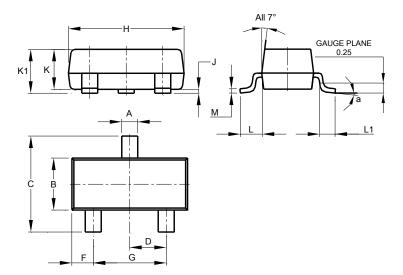
Typical Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)





Package Outline Dimensions

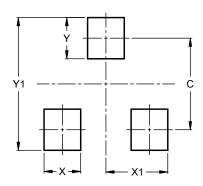
Please see http://www.diodes.com/package-outlines.html for the latest version.



	SOT23						
Dim	Min	Max	Тур				
Α	0.37	0.51	0.40				
В	1.20	1.40	1.30				
С	2.30	2.50	2.40				
D	0.89	1.03	0.915				
F	0.45	0.60	0.535				
G	1.78	2.05	1.83				
Н	2.80	3.00	2.90				
J	0.013	0.10	0.05				
K	0.890	1.00	0.975				
K1	0.903	1.10	1.025				
L	0.45	0.61	0.55				
L1	0.25	0.55	0.40				
М	0.085	0.150	0.110				
а	0°	8°					
All	All Dimensions in mm						

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.



Dimensions	Value (in mm)
С	2.0
X	0.8
X1	1.35
Υ	0.9
Y1	2.9



IMPORTANT NOTICE

DIODES INCORPORATED MAKES NO WARRANTY OF ANY KIND, EXPRESS OR IMPLIED, WITH REGARDS TO THIS DOCUMENT, INCLUDING, BUT NOT LIMITED TO, THE IMPLIED WARRANTIES OF MERCHANTABILITY AND FITNESS FOR A PARTICULAR PURPOSE (AND THEIR EQUIVALENTS UNDER THE LAWS OF ANY JURISDICTION).

Diodes Incorporated and its subsidiaries reserve the right to make modifications, enhancements, improvements, corrections or other changes without further notice to this document and any product described herein. Diodes Incorporated does not assume any liability arising out of the application or use of this document or any product described herein; neither does Diodes Incorporated convey any license under its patent or trademark rights, nor the rights of others. Any Customer or user of this document or products described herein in such applications shall assume all risks of such use and will agree to hold Diodes Incorporated and all the companies whose products are represented on Diodes Incorporated website, harmless against all damages.

Diodes Incorporated does not warrant or accept any liability whatsoever in respect of any products purchased through unauthorized sales channel. Should Customers purchase or use Diodes Incorporated products for any unintended or unauthorized application, Customers shall indemnify and hold Diodes Incorporated and its representatives harmless against all claims, damages, expenses, and attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized application.

Products described herein may be covered by one or more United States, international or foreign patents pending. Product names and markings noted herein may also be covered by one or more United States, international or foreign trademarks.

This document is written in English but may be translated into multiple languages for reference. Only the English version of this document is the final and determinative format released by Diodes Incorporated.

LIFE SUPPORT

Diodes Incorporated products are specifically not authorized for use as critical components in life support devices or systems without the express written approval of the Chief Executive Officer of Diodes Incorporated. As used herein:

- A. Life support devices or systems are devices or systems which:
 - 1. are intended to implant into the body, or
 - 2. support or sustain life and whose failure to perform when properly used in accordance with instructions for use provided in the labeling can be reasonably expected to result in significant injury to the user.
- B. A critical component is any component in a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or to affect its safety or effectiveness.

Customers represent that they have all necessary expertise in the safety and regulatory ramifications of their life support devices or systems, and acknowledge and agree that they are solely responsible for all legal, regulatory and safety-related requirements concerning their products and any use of Diodes Incorporated products in such safety-critical, life support devices or systems, notwithstanding any devices- or systems-related information or support that may be provided by Diodes Incorporated. Further, Customers must fully indemnify Diodes Incorporated and its representatives against any damages arising out of the use of Diodes Incorporated products in such safety-critical, life support devices or systems.

Copyright © 2017, Diodes Incorporated

www.diodes.com